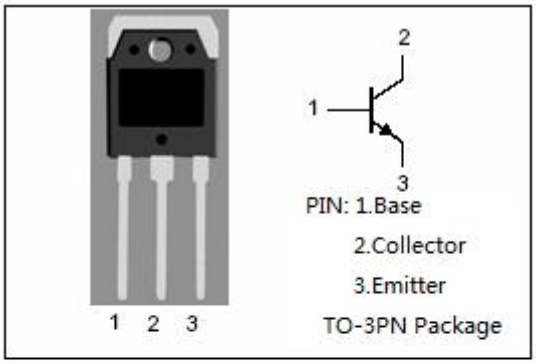
isc Silicon NPN Power Transistor — 2SD1241

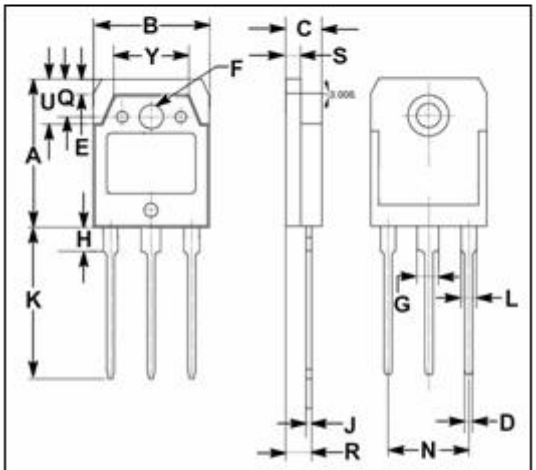


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 60V(Min)
- High Current Capability
- Excellent Safe Operating Area
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching regulators
- Power amplifiers .



DIM	mm MIN	mm MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @T_C=25℃	60	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_B= 0	60		
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	60		
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	10		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 60V; I_E= 0		0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 60V; I_B= 0		0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0		0.1	mA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 3V	70	280	
h_{FE-2}	DC Current Gain	I_C= 5A ; V_{CE}= 3V	30		
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 5V	10		MHz